

NOVEL ACRYLIC MONOMER, NOVEL ACRYLIC POLYMER, RESIST COMPOSITION AND PATTERN FORMING METHOD USING SAME

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Abstract of JP11271974

PROBLEM TO BE SOLVED: To obtain a resist compsn. which can be exposed even at short wavelength, gives stable pattern characteristics and is excellent in dry etching resistance and transparency by using a specified monomer.

SOLUTION: The resist compsn. contains a polymer of a monomer represented by the formula and an acid generating agent. In the formula, R is H or 1-3C optionally substd. alkyl, R' is 1-6C optionally substd. alkyl and Z is plural atoms required to complete an optionally substd. alicyclic hydrocarbon group having at least two norbornane skeletons in combination with C. The resist compsn. may further contain other additives such as amines. When amines are used, resist characteristics such as resolution, pattern shape and mask linearity can be enhanced even if active light of short wavelength such as ArF excimer laser is used as a light source for exposure.

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